A virtual reactor for simulation of plasma enhanced chemical vapor deposition

Krzhizhanovskaya, V.V.

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Chapter 10. Publications*

1. V.V. Korkhov, V.V. Krzhizhanovskaya, J.T. Moscicki. Dynamic Workload Balancing of Parallel Applications with User-Level Scheduling on the Grid. Accepted for publication in the Future Generation Computer Systems. 2008

2. V.V. Korkhov, J.T. Moscicki and V.V. Krzhizhanovskaya. User-Level Scheduling of Divisible Load Parallel Applications with Resource Selection and Adaptive Workload Balancing on the Grid. Accepted for publication in the IEEE Systems Journal, Special Issue on Grid Resource Management. 2008

3. J.K. Rath, A. Verkerk, M. Brinza, R.E.I. Schropp, W.I. Goedheer, V.V. Krzhizhanovskaya, Y.E. Gorbachev, K.E. Orlov, E.M. Khilkevitch, A.S. Smirnov. Gas phase considerations for the deposition of thin film silicon cells by VHF-PECVD at low substrate temperatures. Accepted at the 33rd IEEE PVSEC.

4. A. Verkerk, J.K. Rath, M. Brinza, R.E.I. Schropp, W.I. Goedheer, V.V. Krzhizhanovskaya, Y.E. Gorbachev, K.E. Orlov, E.M.Khilkevitch, A.S. Smirnov. Compensation of decreased ion energy by increased hydrogen dilution in plasma deposition of thin film silicon solar cells at low substrate temperatures. Accepted at the Symposium K of the EMRS spring meeting.


9. V.V. Krzhizhanovskaya, Y.E. Gorbachev, M.A. Zatevakhin and P.M.A. Sloot, "Virtual Reactor" – Computational Environment for Multidimensional Simulation of Plasma

* Listed in reverse chronological order


12. V.V. Krzhizhanovskaya. Software Environment for Simulation of Plasma-Chemical Deposition Reactors on Heterogeneous Computational Resources of the Grid. Proceedings of the conference on Computer Technologies in Modern Researches, Polytechnic Symposium "Young Scientists to the industry of Northwest Russia". December 2006. Publ: St. Petersburg State Polytechnic University 2006, pp. 81-82. ISBN 5-7422-1365-4. Best presentation award.


17. V.V. Krzhizhanovskaya and V.V. Korkhov. Problem-Solving Environments for Simulation and Optimization on Heterogeneous Distributed Computational Resources of the Grid. Proceedings of the Third International Conference on Parallel Computations and Control Problems PACO '2006, Moscow, Russia, October 2-4, 2006. Publ: Moscow, V.A. Trapeznikov Institute of Control Sciences RAS, 2006. pp. 917-932. ISBN 5-201-14990-1.

18. V.V. Krzhizhanovskaya, V.V. Korkhov, P.M.A. Sloot. Virtual Reactor: a distributed computing environment for simulation of plasma chemical processes on heterogeneous resources of the Grid. All-Russian conference "Scientific services on the Internet: Parallel Programming Technologies". Novorossiysk, Russia, 18-23 September 2006

19. Y.E. Gorbachev, A.I. Zhmakin, M.A. Zatevakhin, V.V. Krzhizhanovskaya, M.V. Bogdanov, A.V. Kulik, D.H. Ofengeim, M.S. Ramm. From Electronic Textbooks to Virtual Laboratories. Telecommunications and Informatization in Education, N 5 (36), 2006. Publ: SGU, Moscow (in Russian)


25. V.V. Krzhizhanovskaya, P.M.A. Sloot and Y.E. Gorbachev. Grid-based Simulation of Industrial Thin-Film Production. Simulation: Transactions of the Society for Modeling and Simulation International, Special Issue on Applications of Parallel and Distributed
26. V.V. Krzhizhanovskaya, Y.E. Gorbachev and P.M.A. Sloat. A Grid-Based Problem-Solving Environment for Simulation of Plasma Enhanced Chemical Vapor Deposition. Proceedings of the International Conference "Distributed Computing and Grid Technologies in Science and Education". Publ: JINR, Dubna, 2004, pp. 262-271

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35. V.V. Krzhizhanovskaya, M.A. Zatevakhin, A.A. Ignatiev, Y.E. Gorbachev, P.M.A. Sloot. Distributed Simulation of Silicon-Based Film Growth. Proceedings of the Fourth International Conference on Parallel Processing and Applied Mathematics (PPAM 2001) Naleczow, Poland, September 9-12, 2001, in series Lecture Notes in Computer Science, Vol. 2328, pp. 879-888. Springer-Verlag 2002. ISBN: 3-540-43792-4 . ISSN: 0302-9743 http://www.springerlink.com/content/erj5rtybb3030pe6/


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